BUK758R3-40E

N-channel TrenchMOS standard level FET

11 September 2012 **Product data sheet**

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a SOT78 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

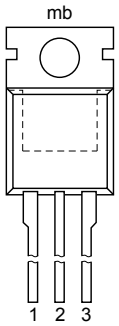
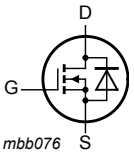
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	40	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 1	[1]	-	-	75	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	-	96	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 20 A; T_j = 25 °C; Fig. 11		-	5.8	7.4	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 20 A; V_{DS} = 32 V; Fig. 13; Fig. 14		-	7.4	-	nC

[1] Continuous current is limited by package.

Scan or click this QR code to view the latest information for this product

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-220AB (SOT78A)	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK758R3-40E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

4. Marking

Table 4. Marking codes

Type number	Marking code
BUK758R3-40E	BUK758R3-40E

5. Limiting values

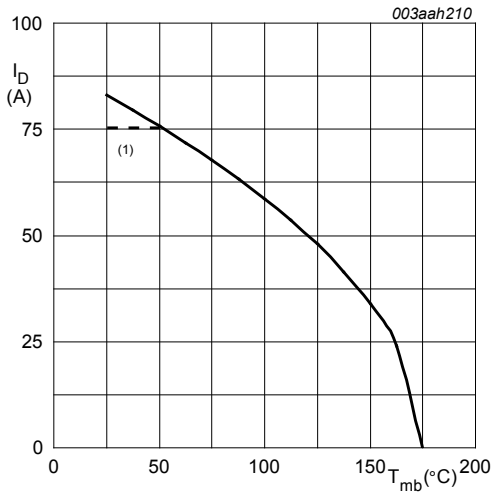
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	40	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ		-	40	V
V_{GS}	gate-source voltage	$T_j \leq 175$ °C; DC		-20	20	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; Fig. 1	[1]	-	75	A
		T_{mb} = 100 °C; V_{GS} = 10 V; Fig. 1	[1]	-	59	A
I_{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \leq 10$ µs; Fig. 4		-	331	A

Symbol	Parameter	Conditions		Min	Max	Unit
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	96	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[1]	-	75	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C		-	331	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \leq 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[2][3]	-	44	mJ

[1] Continuous current is limited by package.
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
[3] Refer to application note AN10273 for further information.



(1) Capped at 75A due to package

Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10V$$

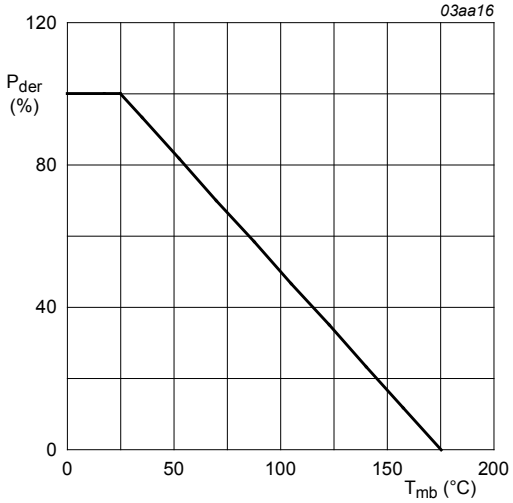


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

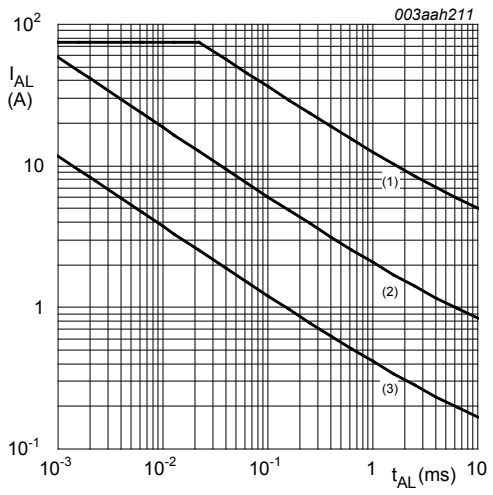


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j\ (init)} = 25°C$; (2) $T_{j\ (init)} = 150°C$; (3) Repetitive Avalanche

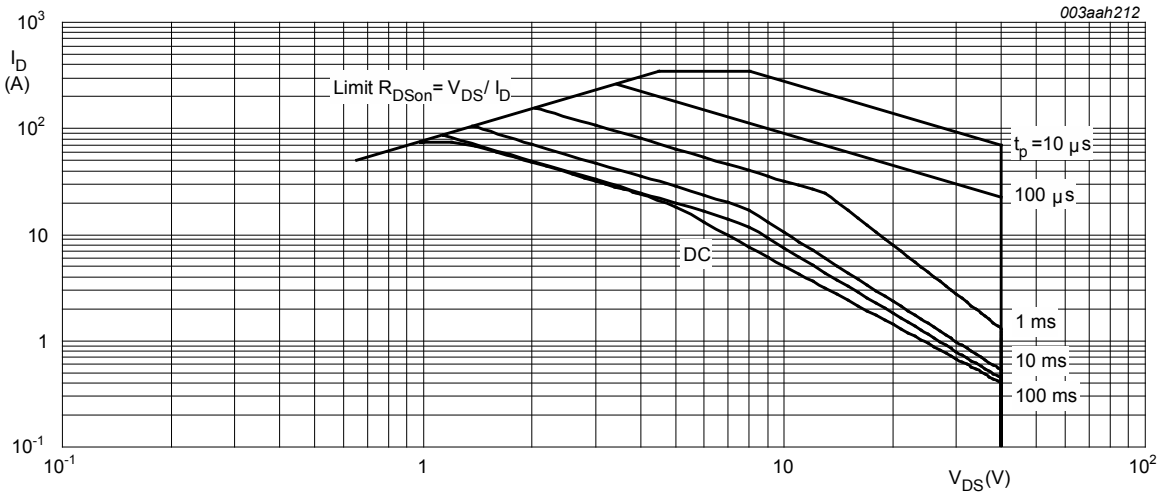


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25°C$; I_{DM} is a single pulse

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	-	1.56	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	vertical in still air		-	60	-	K/W

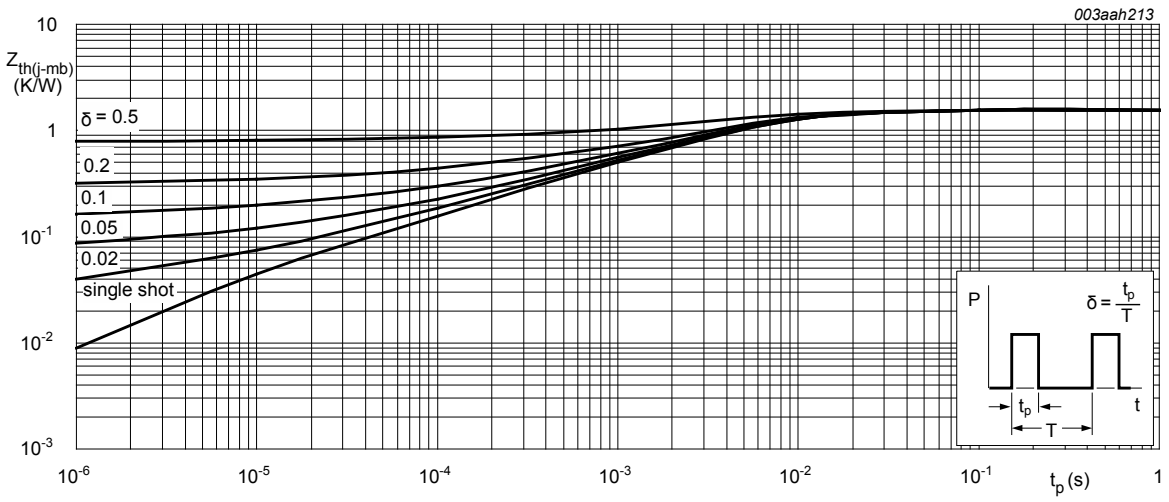


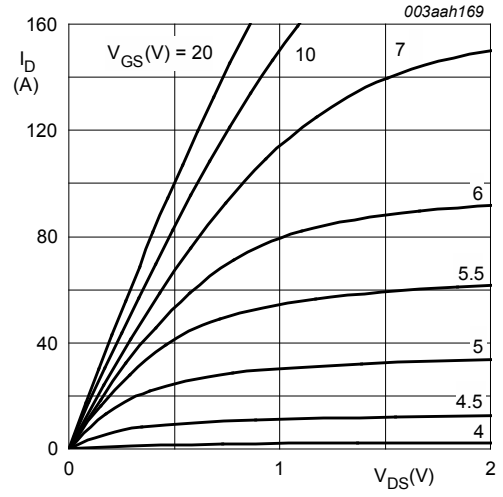
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

7. Characteristics

Table 7. Characteristics

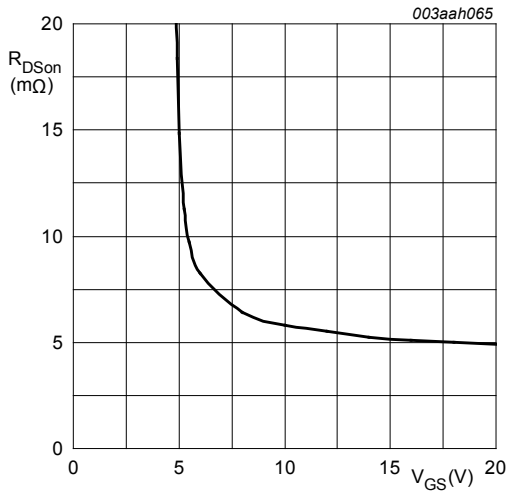
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		40	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 9; Fig. 10		2.4	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 10		-	-	4.5	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 10		1	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C		-	0.05	1	µA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 20 A; T_j = 25 °C; Fig. 11		-	5.8	7.4	mΩ
		V_{GS} = 10 V; I_D = 20 A; T_j = 175 °C; Fig. 12; Fig. 11		-	-	14.1	mΩ
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 20 A; V_{DS} = 32 V; V_{GS} = 10 V; Fig. 13; Fig. 14		-	24	-	nC
Q_{GS}	gate-source charge			-	5.6	-	nC
Q_{GD}	gate-drain charge			-	7.4	-	nC

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; Fig. 15		-	1300	1730	pF
C_{oss}	output capacitance			-	260	312	pF
C_{rss}	reverse transfer capacitance			-	144	197	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.5 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω		-	11	-	ns
t_r	rise time			-	9	-	ns
$t_{d(off)}$	turn-off delay time			-	21	-	ns
t_f	fall time			-	9	-	ns
L_D	internal drain inductance	from upper edge of drain mounting base to center of die		-	2.5	-	nH
L_S	internal source inductance	from source lead to source bonding pad		-	7.5	-	nH
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 20 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 16		-	0.86	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 25 V		-	18.6	-	ns
Q_r	recovered charge			-	10.7	-	nC



T_j = 25 °C; t_p = 300 µs

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values



$T_j = 25°C;\ I_D = 20A$

Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

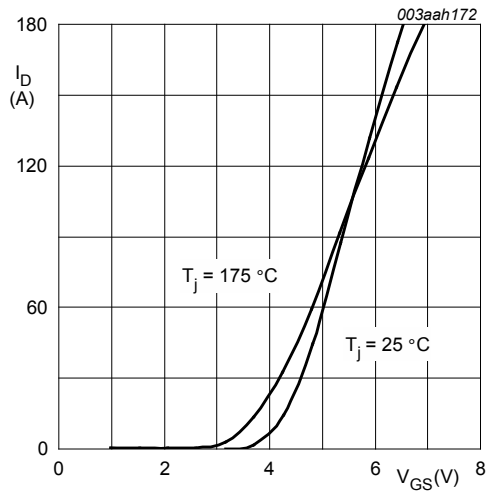


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$

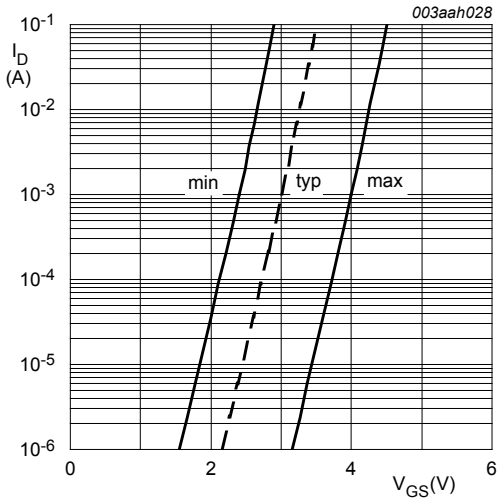


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25°C;\ V_{DS} = 5V$

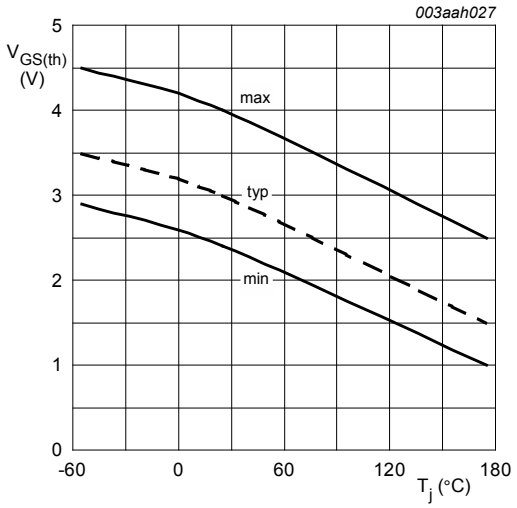
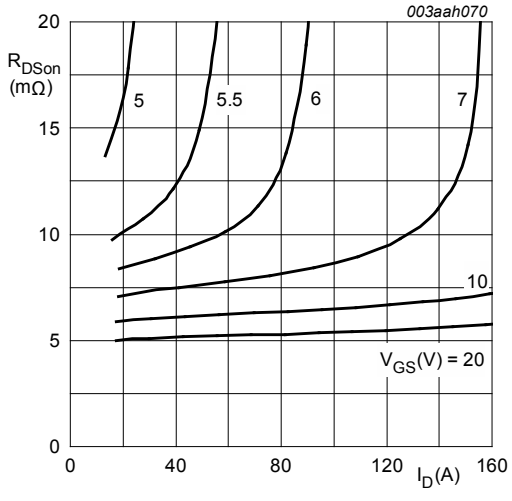


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\ \text{mA};\ V_{DS} = V_{GS}$



T_j = 25 °C; t_p = 300 µs

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

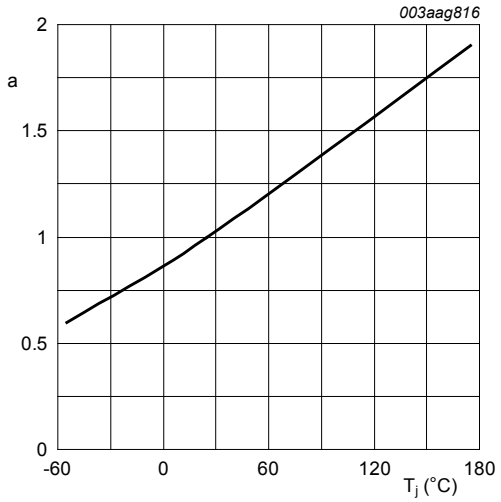


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25\,°C)}}$$

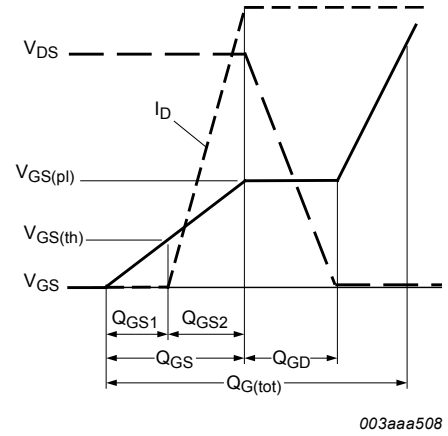


Fig. 13. Gate charge waveform definitions

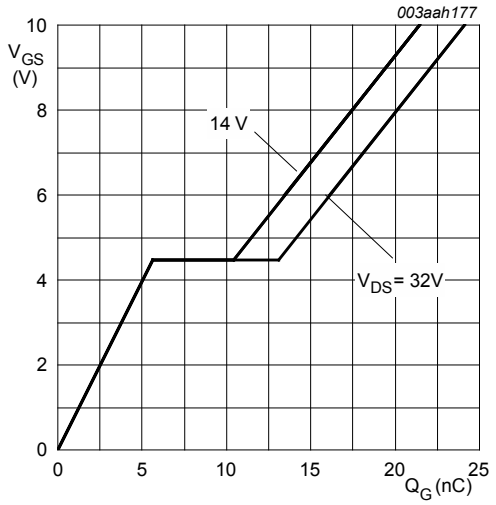


Fig. 14. Transient thermal impedance from junction to mounting base as a function of pulse duration

$T_j = 25°C;\ I_D = 15A$

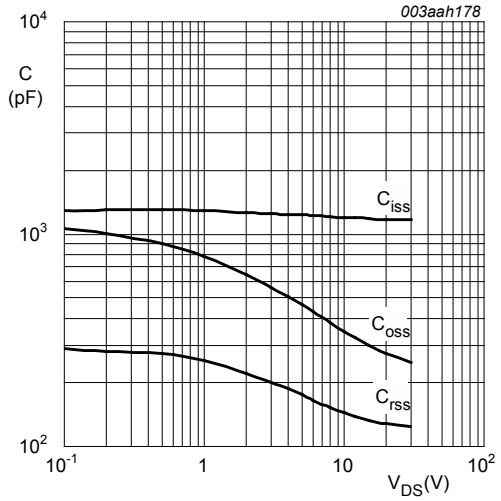


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V;\ f = 1MHz$

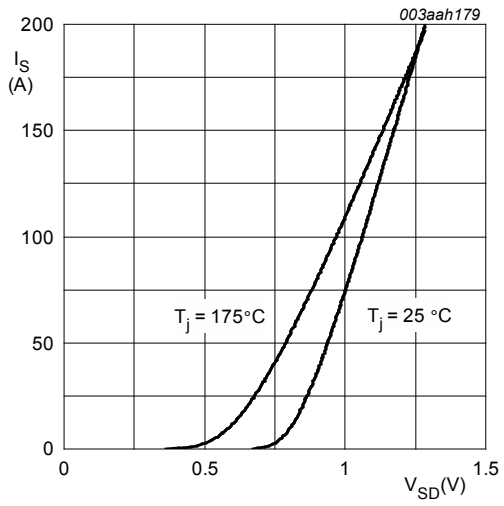
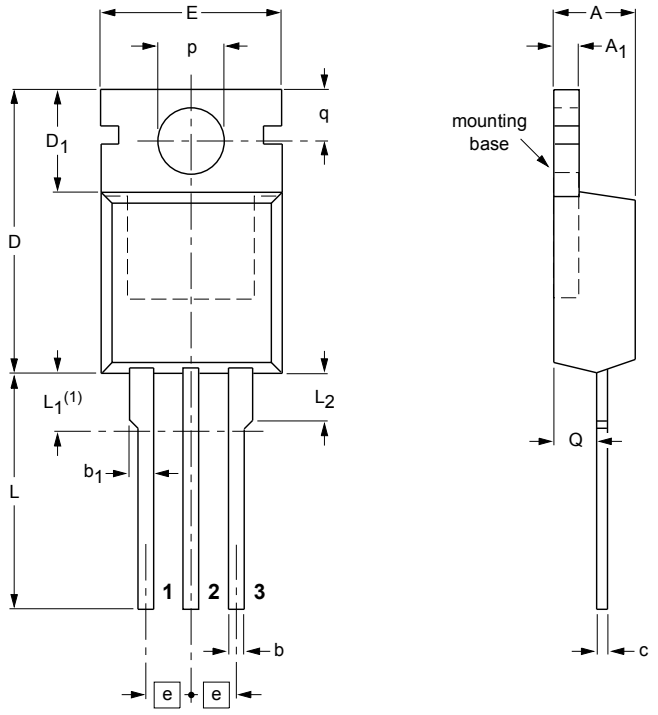


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0\,V$

8. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78A**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	c	D	D_1	E	e	L	L_1(1)	L_2 max.	p	q	Q
mm	4.5 4.1	1.39 1.27	0.9 0.6	1.3 1.0	0.7 0.4	15.8 15.2	6.4 5.9	10.3 9.7	2.54	15.0 13.5	3.30 2.79	3.0	3.8 3.6	3.0 2.7	2.6 2.2

Note

1. Terminals in this zone are not tinned.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78A		3-lead TO-220AB	SC-46			~~03-01-22~~ 05-03-14

Fig. 17. Package outline TO-220AB (SOT78A)

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 11 September 2012